L Number	Hits	Search Text	DB	Time stamp
1	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
	İ		IBM_TDB	
2	0	5233291.pn. and synthesis	USPAT;	[2002/12/10 10:08
	,		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
3	0	5233291.pn. and switch\$5	USPAT;	2002/12/10 10:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		5022001	IBM_TDB	2002/12/10 10:12
4	0	5233291.pn. and select\$5	USPAT;	2002/12/10 10:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
5	155	(("metal/insulator/semiconductor") or	IBM_TDB USPAT;	2002/12/10 10:13
3	155	("metal-insulator-semiconductor")or	US-PGPUB;	2002/12/10 10.13
ł		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
•		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM TDB	
		(capacit \$4/voltage)) and characteristic \$5	1011_100	
		and capacit\$5		
6	107	((("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:15
	10,	("metal-insulator-semiconductor")or	US-PGPUB;	2002, 12, 10 10, 10
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	ļ
		(capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	_	
		and capacit\$5) and (switch\$5 or select\$5)		1
7	54		USPAT;	2002/12/10 10:28
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
ł		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and ((switch\$5 or	1	
		select\$5) same (capacit\$5))		0000/10/10 10 55
8	122	1 ' ' '	USPAT;	2002/12/10 10:30
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
1.		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	IBM_TDB	
		and capacit\$5) and ((switch\$5 or select\$5		
		or elect\$5) same (capacit\$5))		
9	68	(((("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:30
	"	("metal-insulator-semiconductor") or	US-PGPUB;	2002, 12, 10 10.50
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and ((switch\$5 or select\$5		
		or elect\$5) same (capacit\$5))) not		
		(((("metal/insulator/semiconductor") or	1	
		("metal-insulator-semiconductor")or	1	j
		("MIS") or ("MAIS")) same (("C-V") or (CV)		
		or (capacit\$4 adj voltage) or	İ	
		(capacit\$4-voltage) or		
		(capacit\$4/voltage)) and characteristic\$5		·
		and capacit\$5) and ((switch\$5 or		
1		select\$5) same (capacit\$5)))		

_	46	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 12:03
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same ((("C-V") or (CV)) near3	EPO; JPO;	
		characteristic\$5) same capacit\$5	DERWENT;	
J		Characteristicas) same capacitas	IBM TDB	
		449 - 1 241 - 2 1 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4		2002/12/09 11:46
-	37	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 11:46
		("metal-insulator-semiconductor")or	US-PGPUB;	
!		("MIS")) and ("LCR" adj meter)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	"4083254".PN.	USPAT;	2002/12/09 11:50
			US-PGPUB	
. <u>-</u>	1	"4322979".PN.	USPAT;	2002/12/09 11:50
ļ	_	1022373 72111	US-PGPUB	1
	1	"4681451".PN.	USPAT;	2002/12/09 11:50
	1	4001431 .FN.	US-PGPUB	2002/12/03 11.50
			1	0000/10/00 14 03
	72	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:03
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same ((("C-V") or (CV) or	EPO; JPO;	
; i	1	(capacit\$4 adj voltage) or	DERWENT;	1
ı		(capacit\$4-voltage) or	IBM TDB	
1		(capacit\$4/voltage)) near3	<u> </u>	
Ì		characteristic\$5) same capacit\$5		
	3	5701088.bi,uref.	USPAT;	2002/12/09 13:37
 	1	3701000.DI, dle1.	US-PGPUB;	2002/12/03 13.3.
Ì				
Ì			EPO; JPO;	ļ
Ì			DERWENT;	
Ì			IBM_TDB	
_	4	"6177826"	USPAT;	2002/12/09 12:34
Ì			US-PGPUB;	1
!			EPO; JPO;	
	}		DERWENT;	
			IBM TDB	
l _	23	"5175445"	USPĀT;	2002/12/09 12:35
	23	31/3443	US-PGPUB;	2002, 22, 03
			EPO; JPO;	
i				
			DERWENT;	
			IBM_TDB	0000 (10 (00 10 07
-	3	(("6177826") or ("5175445") or	USPAT;	2002/12/09 12:35
	1	("5107137")).PN.	US-PGPUB	
-	14	5233291.bi,uref.	USPAT;	2002/12/09 14:00
			US-PGPUB;	i
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	2	5233291.pn.	USPĀT;	2002/12/10 10:03
-	2	5655571. pii.	US-PGPUB;	1 -002, 12, 10 10.00
			1	1
i .			EPO; JPO;	1
	1			
			DERWENT;	
			DERWENT; IBM_TDB	
	1	"5065103".PN.	DERWENT; IBM_TDB USPAT;	2002/12/09 14:00
_	1	"5065103".PN.	DERWENT; IBM_TDB	2002/12/09 14:00
-	1	"5065103".PN.	DERWENT; IBM_TDB USPAT;	2002/12/09 14:00 2002/12/09 14:01
-			DERWENT; IBM_TDB USPAT; US-PGPUB	
-	1	"4992728".PN.	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01
-			DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	
- -	1	"4992728".PN. "4941753".PN.	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01
- - -	1	"4992728".PN.	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN.	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01
- - -	1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("MIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01
- - -	1 1 1	"4992728".PN. "4941753".PN. "4891584".PN. (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same (("C-V") or (CV) or	DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/09 14:01 2002/12/09 14:01 2002/12/09 14:01

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-	155	(("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:12
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	IBM_TDB	
		and capacit\$5	<u>.</u>	
1_	12	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:35
	12	("metal-insulator-semiconductor")or	US-PGPUB;	2002, 22, 33
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and synthesis		
-	53	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:43
		("metal-insulator-semiconductor") or	US-PGPUB;	
[("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO; DERWENT;	
		or (capacit\$4 adj voltage) or (capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	15155	
] .		and capacit\$5) and "nm"		
_	1	5233291.pn. and "MIS"	USPAT;	2002/12/09 15:29
		•	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/00 15 00
-	2	5233292.pn.	USPAT;	2002/12/09 15:30
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	5233291.pn.	USPAT;	2002/12/09 15:43
		3233231.pii.	US-PGPUB;	2000, 12, 03
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 15:44
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
j		or (capacit\$4 adj voltage) or	DERWENT;	
		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	IBM_TDB	
		and capacit\$5) and (("4083254".PN. or		6 1
		three) adj nm)		•
_	9	(("4083254".PN. or three) adj nm)	USPAT;	2002/12/10 07:14
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	1	5000001	IBM_TDB	2002/12/10 07:07
-	1	5233291.pn. and MIS	USPAT;	2002/12/10 07:27
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6860	motohiro.in.	USPAT;	2002/12/10 07:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6828	motohiro.inv.	USPAT;	2002/12/10 07:28
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
! _		motohiro.inv. and ("MAIS")	IBM_TDB USPAT;	2002/12/10 07:50
1-	•	motonitio.inv. and (MAIS)	US-PGPUB;	2002,12,10 07.50
			EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	
L	<u> </u>	<u> </u>	1	L